

WHAT IS CLAIMED IS:

1. A quality monitoring system for building structure, comprising:

a semiconductor integrated circuit device which
5 is built in the building structure and in which sensors for detecting physical quantity related to the property of the building structure are mounted; and

an inspection device that receives a detect signal generated based upon the physical quantity
10 detected by the semiconductor integrated circuit device and determines the quality of the building structure based upon the received detect signal.

2. A quality monitoring system for building structure according to Claim 1, wherein:

15 the semiconductor integrated circuit device is provided with a memory;

the memory stores an ID number proper to the semiconductor integrated circuit device; and

the semiconductor integrated circuit device
20 transmits the ID number together with the detect signal to the inspection device.

3. A quality monitoring system for building structure according to Claim 1, wherein:

the semiconductor integrated circuit device is
25 provided with a memory;

the memory stores a detect signal corresponding to the detected physical quantity; and

the semiconductor integrated circuit device reads

the detect signal from the memory according to a request from the inspection device and transmits it to the inspection device.

4. A quality monitoring system for building structure according to Claim 1, wherein:

the detect signal is transmitted from the semiconductor integrated circuit device to the inspection device by radio.

5. A quality monitoring system for building structure according to Claim 1, wherein:

the building structure is mainly made of concrete;

the semiconductor integrated circuit device is built in the building structure in a state of paste before the concrete is set; and

the semiconductor integrated circuit device detects the physical quantity of the concrete in the state of paste and transmits the detect signal to the inspection device.

6. A quality monitoring method for building structure, comprising steps of:

a step for detecting physical quantity related to the property of the building structure and building a semiconductor integrated circuit device mounting a sensor for generating a detect signal corresponding to the physical quantity in the building structure;

a step for operating the sensor, detecting the physical quantity related to the property of the

building structure and generating the detect signal
corresponding to the physical quantity;

5 a step for transmitting the detect signal to an
inspection device provided outside the semiconductor
integrated circuit device; and

a step for determining the quality of the
building structure based upon the detect signal
received by the inspection device.

10 7. A quality monitoring method for building
structure according to Claim 6, wherein:

the semiconductor integrated circuit device
further mounts a memory; and

the quality monitoring method for building
structure further comprises steps of:

15 a step for storing the detect signal generated by
the sensor in the memory; and

a step for reading the detect signal stored in
the memory.

20 8. A quality monitoring method for building
structure according to Claim 7, wherein:

the step for reading the detect signal is a step
for reading the detect signal stored in the memory
according to a request from the inspection device.

25 9. A quality monitoring method for building
structure according to Claim 7, wherein:

the step for transmitting the detect signal to an
inspection device provided outside the semiconductor
integrated circuit device is a step for transmitting an

ID number proper to the semiconductor integrated circuit device and stored in the memory together with the detect signal; and

the step for determining the quality is a step
5 for specifying a semiconductor integrated circuit device that transmits the detect signal based upon the ID number transmitted from the semiconductor integrated circuit device together with the detect signal and determining the quality of the building structure.

10 10. A quality monitoring method for building structure according to Claim 9, wherein:

the step for specifying a semiconductor integrated circuit device that transmits the detect signal and determining the quality of the building
15 structure is a step detecting the position of the semiconductor integrated circuit device in the building structure and determining the quality of the building structure.

11. A quality monitoring method for building
20 structure according to Claim 6, wherein:

the step for transmitting the detect signal to an inspection device provided outside the semiconductor integrated circuit device is a step for transmitting the detect signal from the semiconductor integrated
25 circuit device to the inspection device by radio.

12. A quality monitoring method for building structure according to Claim 6, wherein:

the building structure is mainly made of

concrete;

the step for building the semiconductor integrated circuit device in the building structure is a step for building the semiconductor integrated circuit device in the building structure in a state of paste before the concrete is set;

the step for generating the detect signal is a step for operating the sensor in a state of paste before the concrete is set, detecting the physical quantity related to the property of the building structure and generating the detect signal corresponding to the physical quantity; and

the step for transmitting the detect signal to an inspection device provided outside the semiconductor integrated circuit device is a step for transmitting the detect signal to the inspection device after the concrete is set.

13. A quality monitoring method for building structure according to Claim 6, wherein:

the sensor includes at least one of an electric resistance sensor, a temperature sensor, a pressure sensor and an acceleration sensor.

14. A semiconductor integrated circuit device, comprising:

a sensor that detects physical quantity measurable by a semiconductor and related to the property of building structure;

an A/D converter that amplifies a signal detected

by the sensor and converts the signal to a digital signal;

a microprocessor that processes the digital signal;

5 a transmitter circuit that transmits a signal processed by the microprocessor to an external device;

an electric power generator configured so that it supplies electric power to at least one of the sensor, the A/D converter, the microprocessor and the

10 transmitter circuit;

an electric power controller that controls whether electric power generated by the electric power generator is supplied to at least one of the sensor, the A/D converter, the microprocessor and the

15 transmitter circuit or not; and

a capacitor configured so that electric power generated by the electric power generator is stored.

15. A semiconductor integrated circuit device according to Claim 14, further comprising:

20 a memory for storing information acquired by the sensor.

16. A semiconductor integrated circuit device according to Claim 15, wherein:

the memory stores an ID number proper to a

25 semiconductor integrated circuit device mounting the memory.

17. A semiconductor integrated circuit device according to Claim 14, wherein:

the sensor includes a pressure sensor.

18. A semiconductor integrated circuit device according to Claim 14, wherein:

the transmitter circuit transmits using a pulse
5 train in an ultra wide band (UWB) telecommunication system.

19. A semiconductor integrated circuit device according to Claim 14, wherein:

the electric power generator comprises:

10 a variable capacitor formed in an MEMS process;
and

an electric power scavenging circuit that
scavenges the increase of the electrostatic energy of
the variable capacitor by the vibration of the building
15 structure and converts it to electrical energy.

20. A semiconductor integrated circuit device according to Claim 14, wherein:

the sensor, the A/D converter, the microprocessor,
the transmitter circuit and the electric power
20 controller are formed on one semiconductor substrate.

21. A semiconductor integrated circuit device according to Claim 14, wherein:

the electric power generator is formed on a
second semiconductor chip separate from a first
25 semiconductor chip where the sensor, the A/D converter,
the microprocessor, the transmitter circuit and the
electric power controller are formed; and

the first semiconductor chip and the second

semiconductor chip are mounted on reverse surfaces of a common substrate.

22. Building structure the quality of which can be determined by a quality monitoring system for building structure, wherein:

the quality monitoring system for building structure comprises:

a semiconductor integrated circuit device which is built in the building structure and in which a sensor for detecting physical quantity related to the property of the building structure is mounted; and

an inspection device that receives a detect signal generated based upon physical quantity detected in the semiconductor integrated circuit device and determines the quality of the building structure based upon the received detect signal; and

the semiconductor integrated circuit device comprises:

a sensor for detecting physical quantity measurable by a semiconductor and related to the property of building structure;

an A/D converter that amplifies a signal detected by the sensor and converts it to a digital signal;

a microprocessor that processes the digital signal;

a transmitter circuit that transmits the signal processed by the microprocessor to an external device;

an electric power generator configured so that it

supplies electric power to at least one of the sensor,
the A/D converter, the microprocessor and the
transmitter circuit;

an electric power controller configured so that
5 it controls whether electric power generated by the
electric power generator is supplied to at least one of
the sensor, the A/D converter, the microprocessor and
the transmitter circuit or not; and

a capacitor configured so that it stores electric
10 power generated by the electric power generator.

23. Building structure in which a semiconductor
integrated circuit device is buried and the quality of
which can be determined by a quality monitoring method
for building structure, wherein:

15 the quality monitoring method for building
structure comprises steps of:

a step for building a semiconductor integrated
circuit device mounting a sensor for detecting physical
quantity related to the property of the building
20 structure and generating a detect signal corresponding
to the physical quantity in the building structure;

a step for operating the sensor, detecting the
physical quantity related to the property of the
building structure and generating the detect signal
25 corresponding to the physical quantity;

a step for transmitting the detect signal to an
inspection device provided outside the semiconductor
integrated circuit device; and

a step for determining the quality of the building structure based upon the detect signal received by the inspection device; and

the semiconductor integrated circuit device
5 comprises:

a sensor for detecting physical quantity measurable by a semiconductor and related to the property of building structure;

an A/D converter that amplifies a signal detected
10 by the sensor and converts it to a digital signal;

a microprocessor that processes the digital signal;

a transmitter circuit that transmits the signal processed by the microprocessor to an external device;

15 an electric power generator configured so that it supplies electric power to at least one of the sensor, the A/D converter, the microprocessor and the transmitter circuit;

an electric power controller configured so that
20 it controls whether electric power generated by the electric power generator is supplied to at least one of the sensor, the A/D converter, the microprocessor and the transmitter circuit or not; and

a capacitor configured so that it stores electric
25 power generated by the electric power generator.

24. Building structure, wherein:

a semiconductor integrated circuit device provided with a sensor for detecting physical quantity

related to the property of the building structure is buried; and

the quality can be determined based upon a detect signal corresponding to the physical quantity detected by the semiconductor integrated circuit device by the inspection device.

25. Building structure according to Claim 24, wherein:

the semiconductor integrated circuit device further comprises:

an A/D converter that amplifies a signal detected by the sensor and converts it to a digital signal;

a microprocessor that processes the digital signal;

a transmitter circuit that transmits the signal processed by the microprocessor to an external device;

an electric power generator configured so that it supplies electric power to at least one of the sensor, the A/D converter, the microprocessor and the transmitter circuit;

an electric power controller configured so that it controls whether electric power generated by the electric power generator is supplied to at least one of the sensor, the A/D converter, the microprocessor and the transmitter circuit or not; and

a capacitor configured so that it stores electric power generated by the electric power generator.